



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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## Features

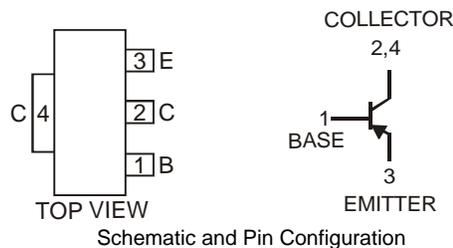
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (NK-DXT651)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications

## Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)



SOT89-3L



## Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Continuous Collector Current	$I_C$	-3	A
Peak Pulse Collector Current	$I_{CM}$	-6	A

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$	$P_D$	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
<b>OFF CHARACTERISTICS (Note 4)</b>						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-80	—	—	V	$I_C = -100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60	—	—	V	$I_C = -10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -100\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CBO}$	—	—	-0.1	$\mu\text{A}$	$V_{CB} = -60\text{V}, I_E = 0$
Emitter Cutoff Current	$I_{EBO}$	—	—	-0.1	$\mu\text{A}$	$V_{CB} = -60\text{V}, I_E = 0, T_A = 100^\circ\text{C}$
<b>ON CHARACTERISTICS (Note 4)</b>						
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.08 -0.2	-0.3 -0.6	V	$I_C = -1\text{A}, I_B = -100\text{mA}$ $I_C = -3\text{A}, I_B = -300\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-0.9	-1.25	V	$I_C = -1\text{A}, I_B = -100\text{mA}$
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	—	-0.8	-1	V	$V_{CE} = -2\text{V}, I_C = -1\text{A}$
DC Current Gain	$h_{FE}$	70 100 80 40	200 180 160 140	— 300 — —	—	$V_{CE} = -2\text{V}, I_C = -50\text{mA}$ $V_{CE} = -2\text{V}, I_C = -500\text{mA}$ $V_{CE} = -2\text{V}, I_C = -1\text{A}$ $V_{CE} = -2\text{V}, I_C = -2\text{A}$
<b>AC CHARACTERISTICS</b>						
Transition Frequency	$f_T$	100	145	—	MHz	$V_{CE} = -10\text{V}, I_C = -50\text{mA}, f = 100\text{MHz}$
Output Capacitance	$C_{obo}$	—	—	30	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Switching Times	$t_{on}$ $t_{off}$	— —	45 200	— —	ns ns	$I_C = -500\text{mA}, V_{CC} = -10\text{V}$ $I_{B1} = I_{B2} = -50\text{mA}$

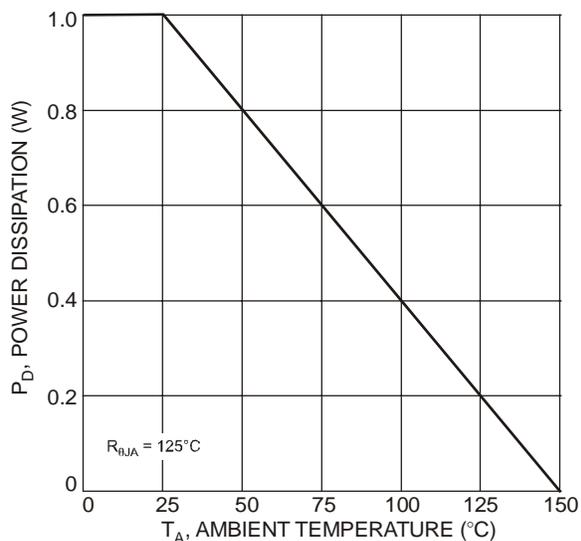
 Notes: 4. Measured under pulsed conditions. Pulse width = 300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$ .


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

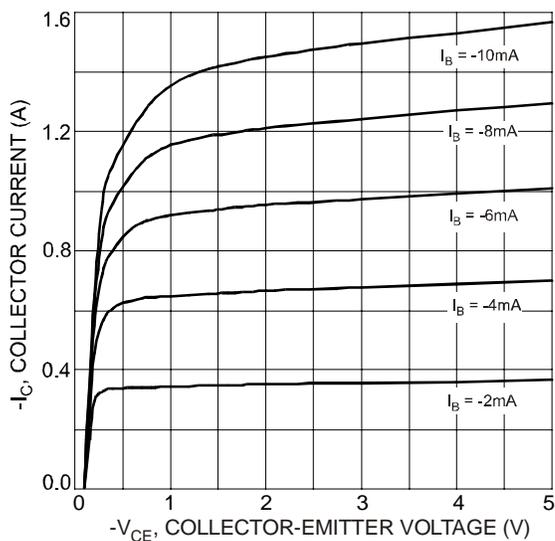


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

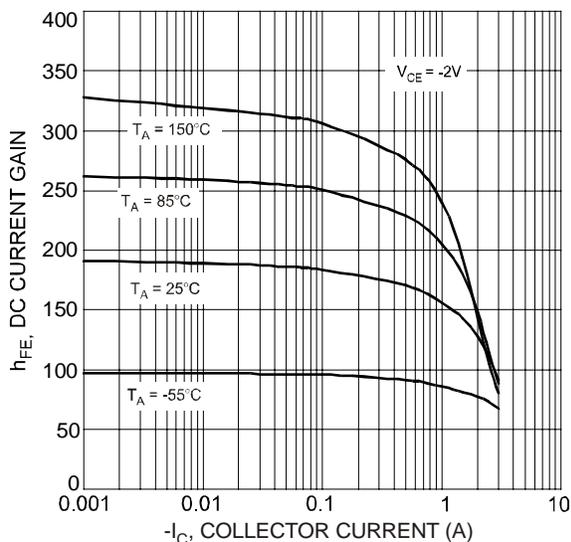


Fig. 3 Typical DC Current Gain vs. Collector Current

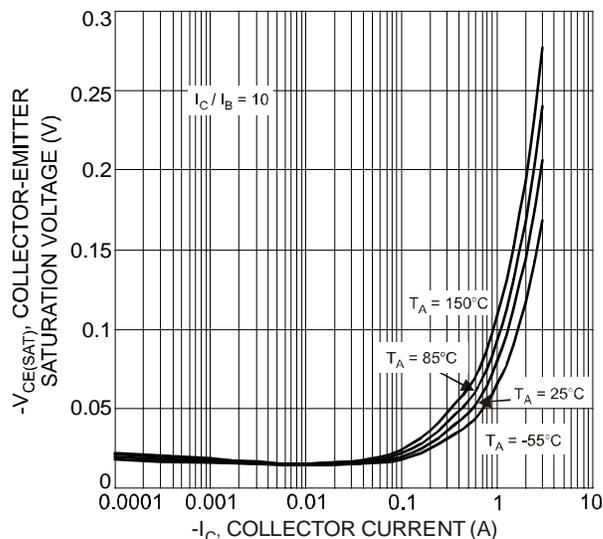


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

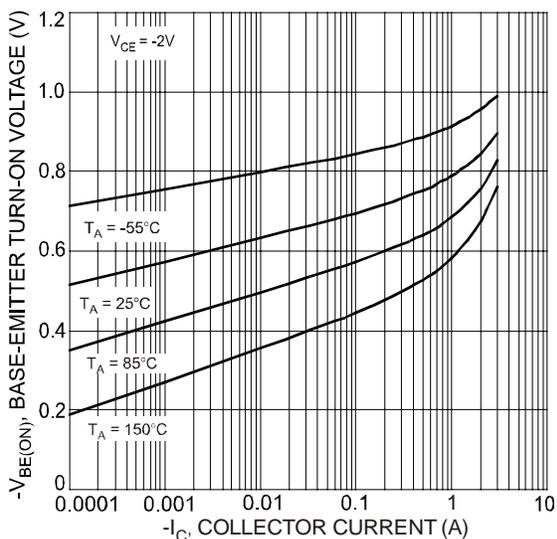


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

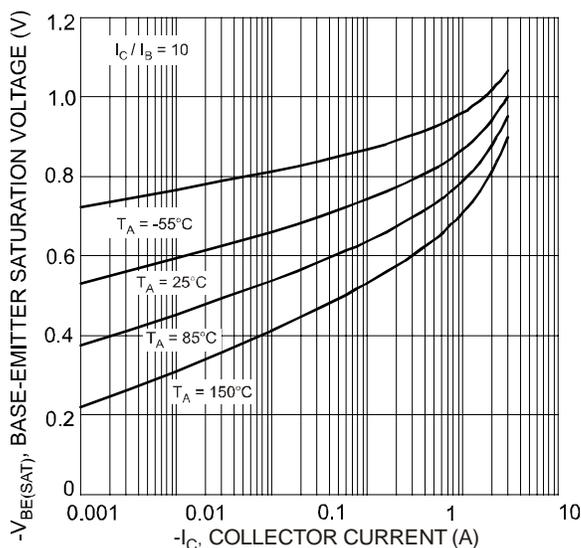


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

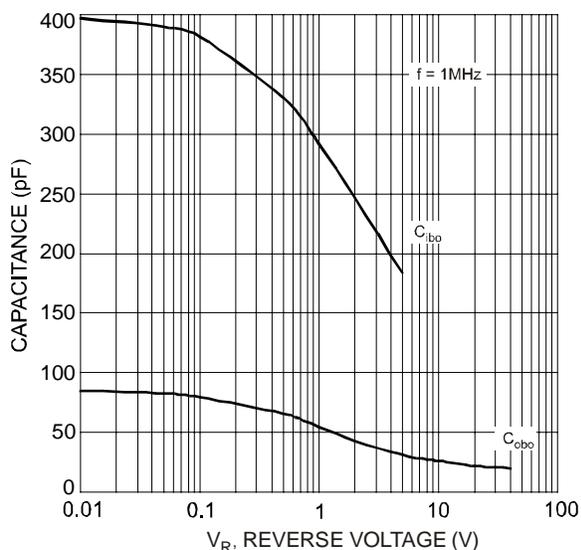


Fig. 7 Typical Capacitance Characteristics

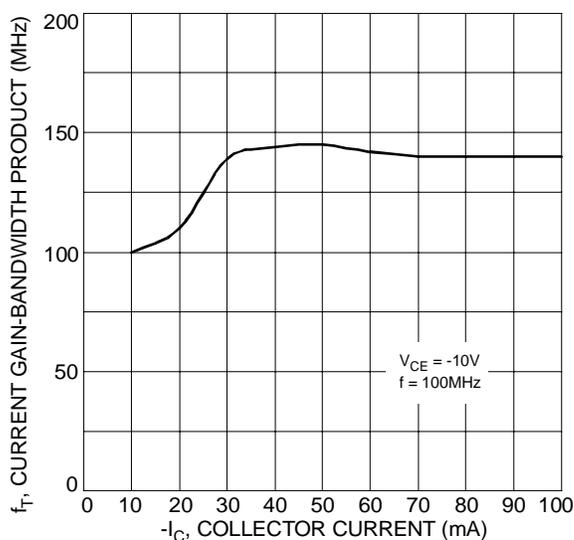
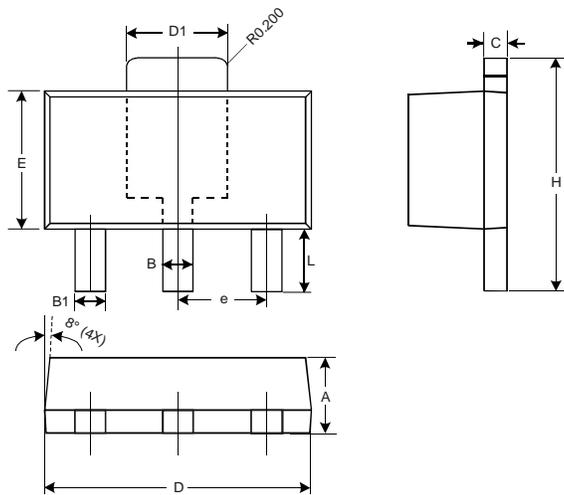


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

### Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

### Suggested Pad Layout

